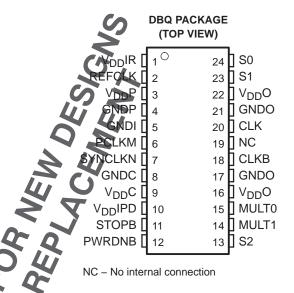
- 400-MHz Differential Clock Source for **Direct Rambus<sup>™</sup> Memory Systems for an** 800-MHz Data Transfer Rate
- Synchronizes the Clock Domains of the **Rambus Channel With an External System** or Processor Clock
- **Three Power Operating Modes to Minimize Power for Mobile and Other Power-Sensitive Applications**
- Operates From a Single 3.3-V Supply and 120 mW at 300 MHz (Typ)
- Packaged in a Shrink Small-Outline Package (DBQ)
- Supports Frequency Multipliers: 4, 6, 8, 16/3
- No External Components Required for PLL
- **Supports Independent Channel Clocking**
- Spread Spectrum Clocking Tracking Capability to Reduce EMI
- Designed for Use With TI's 133-MHz Clock Synthesizers CDC924 and CDC921

#### Cycle-Cycle Jitter Is Less Than 50 ps at 400 MHz

- Certified by Gigatest Labs to Exceed the Rambus DRCG Validation Requirement
- **Supports Industrial Temperature Range of** -40°C to 85°C



#### description

The Direct Rambus clock generator (DRCG) provides the necessary clock signals to support a Direct Rambus memory subsystem. It includes signals to synchronize the Direct Rambus channel clock to an external system or processor clock. It is designed to support Direct Rambus memory on a desktop, workstation, server, and mobile PC motherboards. DRCG also provides an off-the-shelf solution for a broad range of Direct Rambus memory applications.

The DRCG provides clock multiplication and phase alignment for a Direct Rambus memory subsystem to enable synchronous communication between the Rambus channel and ASIC clock domains. In a Direct Rambus memory subsystem, a system clock source provides the REFCLK and PCLK clock references to the DRCG and memory controller, respectively. The DRCG multiplies REFCLK and drives a high-speed BUSCLK to RDRAMs and the memory controller. Geal ratio logic in the memory controller divides the PCLK and BUSCLK frequencies by ratios M and N such that FCLKM = SYNCLKN, where SYNCLK = BUSCLK/4. The DRCG detects the phase difference between PCLKM and SYNCLKN and adjusts the phase of BUSCLK such that the skew between PCLKM and SYNCLKN is minimized. This allows data to be transferred across the SYNCLK/PCLK boundary without incurring additional latency.

User control is provided by inultiply and mode selection terminals. The multiply terminals provide selection of one of four clock frequency multiply ratios, generating BUSCLK frequencies ranging from 267 MHz to 400 MHz with clock references ranging from 33 MHz to 100 MHz. The mode select terminals can be used to select a bypass mode where the frequency multiplied reference clock is directly output to the Rambus channel for systems where synchronization between the Rambus clock and a system clock is not required. Test modes are provided to bypass the PLL and output REFCLK on the Rambus channel and to place the outputs in a high-impedance state for board testing.

The CDCR83 is characterized for operation over free-air temperatures of -40°C to 85°C.

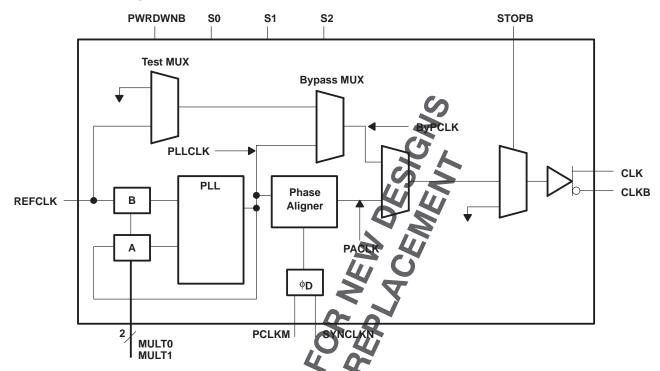


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Direct Rambus and Rambus are trademarks of Rambus Inc.



#### functional block diagram



FUNCTION TABLET

10.00			1 011	HOLLI	
MODE	S0	S1	52/	CLK	CLKB
Normal	0	0	6	Phase aligned clock	Phase aligned clock B
Bypass	1	0	0	PLLCLK	PLLCLKB
Test	1		0	REFCLK	REFCLKB
Output test (OE)	0	H	X	▶ Hi-Z	Hi-Z
Reserved	0	P	6	_	
Reserved	1	0	74	_	_
Reserved		1	1	Hi-Z	Hi-Z

† X = don't care, Hi-Z



#### **Terminal Functions**

NAME NO.  CLK 20  CLKB 18  GNDC 8  GNDI 5  GNDO 17, 21  GNDP 4  MULTO 15  MULT1 14  NC 19  PCLKM 6  PWRDNB 12	O Output clock O Output clock (completed of the completed of the control of the c	er s s s s s s s s s s s s s s s s s s s
CLKB 18  GNDC 8  GNDI 5  GNDO 17, 21  GNDP 4  MULTO 15  MULT1 14  NC 19  PCLKM 6  PWRDNB 12	O Output clock (completed of the completed of the control input of the c	er s s s s s s s s s s s s s s s s s s s
GNDC 8 GNDI 5 GNDO 17, 21 GNDP 4 MULTO 15 MULT1 14 NC 19 PCLKM 6 PWRDNB 12	GND for phase align GND for control inpu GND for clock outpu GND for PLL I PLL multiplier select I PLL multiplier select Not used I Phase detector input	er s s s s s s s s s s s s s s s s s s s
GNDI 5 GNDO 17, 21 GNDP 4 MULTO 15 MULT1 14 NC 19 PCLKM 6 PWRDNB 12	GND for control inpu GND for clock outpu GND for PLL I PLL multiplier select I PLL multiplier select Not used I Phase detector input	
GNDO 17, 21 GNDP 4 MULTO 15 MULT1 14 NC 19 PCLKM 6 PWRDNB 12	GND for clock outpu GND for PLL PLL multiplier select PLL multiplier select Not used Phase detector input	
GNDP 4 MULT0 15 MULT1 14 NC 19 PCLKM 6 PWRDNB 12	GND for PLL  I PLL multiplier select  I PLL multiplier select  Not used  I Phase detector input	
MULTO 15 MULT1 14 NC 19 PCLKM 6 PWRDNB 12	PLL multiplier select     PLL multiplier select     Not used     Phase detector input	
MULT1 14  NC 19  PCLKM 6  PWRDNB 12	I PLL multiplier select Not used I Phase detector input	
NC 19 PCLKM 6 PWRDNB 12	Not used  I Phase detector input	
PCLKM 6 PWRDNB 12	I Phase detector input	
PWRDNB 12		
	I Active low power dov	
		vn
REFCLK 2	I Reference clock	2,4
S0 24	I Mode control	40
S1 23	I Mode control	2.4
S2 13	I Mode control	
STOPB 11	I Active low output dis	able
SYNCLKN 7	I Phase detector input	0 4
V <sub>DD</sub> C 9	V <sub>DD</sub> for phase align	er C
V <sub>DD</sub> IPD 10	Reference voltage for	r phase detector inputs and STOPB
V <sub>DD</sub> IR 1	Reference voltage for	r REFCEK
V <sub>DD</sub> O 16, 22	V <sub>DD</sub> for clock output	s 24 60
V <sub>DD</sub> P 3	V <sub>DD</sub> for PLL	92
	NOT RECOMM	



#### PLL divider selection

Table 1 lists the supported REFCLK and BUSCLK frequencies. Other REFCLK frequencies are permitted, provided that (267 MHz < BUSCLK < 400 MHz) and (33 MHz < REFCLK < 100 MHz).

Table 1. REFCLK and BUSCLK Frequencies

MULT0	MULT1	REFCLK (MHz)	MULTIPLY RATIO	BUSCLK (MHz)
0	0	67	4	267
0	1	50	6	300
0	1	67	6	400
1	1	33	8	267
1	1	50	8	400
1	0	67	16/3	356

## Table 2. Clock Output Driver

STATE	PWRDNB	STOPB	CLK	CLKB
Powerdown	0	Х	GND	GND
CLK stop	1	0	VX, STOP	VX, STOP
Normal	1	1	PACLK PLLCLK/ REFCLK†	PACLKB/PLLCLKB/ REFCLKB

<sup>†</sup> Depending on the state of S0, S1, and S2

## absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage range, V <sub>DD</sub> (see Note 1)	–0.5 V to 4 V
Output voltage range, V <sub>O</sub> , at any output terminal	0.5 V to V <sub>DD</sub> + 0.5 V
Input voltage range, V <sub>I</sub> , at any input terminal	
Continuous total power dissipation	
Operating free-air temperature range	
Storage temperature range, T <sub>stg</sub>	
Lead temperature 1,6 mm (1/16 inch stron) case for 10 seconds	260°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum atings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to the GND terminals.

## DISSIPATION RATING TABLE

PACKAGE	T <sub>A</sub> ≤ 25°C	DERATING FACTOR	T <sub>A</sub> = 70°C	T <sub>A</sub> = 85°C
	POWER RATING	ABOVE T <sub>A</sub> = 25°C <sup>‡</sup>	POWER RATING	POWER RATING
DBQ	1400 mW	11 mW/°C	905 mW	740 mW

<sup>‡</sup>This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.



### recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V <sub>DD</sub>	3.135	3.3	3.465	V
High-level input voltage, V <sub>IH</sub> (CMOS)	$0.7 \times V_{DD}$			V
Low-level input voltage, V <sub>IL</sub> (CMOS)			$0.3 \times V_{DD}$	V
Initial phase error at phase detector inputs (required range for phase aligner)	-0.5×t <sub>C</sub> (PD)	(	$0.5 \times t_{C(PD)}$	
REFCLK low-level input voltage, V <sub>IL</sub>	3	0	$0.3 \times V_{DD}IR$	V
REFCLK high-level input voltage, VIH	$0.7 \times V_{DD}IR$			V
Input signal low voltage, V <sub>IL</sub> (STOPB)	201	0.3	$3 \times V_{DD}IPD$	V
Input signal high voltage, V <sub>IH</sub> (STOPB)	0.7×V <sub>DD</sub> IPD			V
Input reference voltage for (REFCLK) (VDDIR)	1.235		3.465	V
Input reference voltage for (PCLKM and SYSCLKN) (VDDIPD)	1.235		3.465	V
High-level output current, IOH	.7.2		-16	mA
Low-level output current, IOL	6 W		16	mA
Operating free-air temperature, T <sub>A</sub>	-40		85	°C

## timing requirements

out cycle time, t <sub>C(in)</sub> out cycle-to-cycle jitter  out duty cycle over 10,000 cycles  out frequency modulation, f <sub>mod</sub> odulation index, nonlinear maximum 0.5%  asse detector input cycle time (PCLKM and SYNCLKN)  out slew rate, SR  out duty cycle (PCLKM and SYNCLKN)	10 40% 30 30 1 25%	40 250 60% 33 0.6% 100 4 75%	ns ps kHz ns V/ns
out duty cycle over 10,000 cycles out frequency modulation, f <sub>mod</sub> odulation index, nonlinear maximum 0.5% ase detector input cycle time (PCLKM and SYNCLKN) out slew rate, SR	30 30 1	60% 33 0.6% 100 4	kHz
out frequency modulation, f <sub>mod</sub> odulation index, nonlinear maximum 0.5% ase detector input cycle time (PCLKM and SYNCLKN) out slew rate, SR	30 30 1	33 0.6% 100 4	ns
ase detector input cycle time (PCLKM and SYNCLKN)  out slew rate, SR	30	0.6% 100 4	ns
ase detector input cycle time (PCLKM and SYNCLKN) out slew rate, SR	1	100 4	
out slew rate, SR	1	4	
			V/ns
out duty cycle (PCLKM and SYNCLKN)	25%	75%	
555			



## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETE	:R	TEST CON	IDITIONS†	MIN	TYP‡	MAX	UNIT
V <sub>O(STOP)</sub>	Output voltage (STOPB = 0)	e during CLK Stop	See Figure 1		1.1		2	
$V_{O(X)}$	Output crossii	ng-point voltage	See Figure 1 and Fi	gure 6	1.3		1.8	V
Vo	Output voltage	e swing	See Figure 1	5	0.4		0.6	V
V <sub>IK</sub>	Input clamp v	oltage	$V_{DD} = 3.135 \text{ V},$	I <sub>I</sub> = −18 mA			-1.2	V
			See Figure 1	CR			2	
∨он	High-level out	put voltage	$V_{DD}$ = min to max,	I <sub>OH</sub> = −1 mA	V <sub>DD</sub> – 0.1 V			V
			$V_{DD} = 3.135 V,$	I <sub>OH</sub> € € 16 mA	2.4			i
			See Figure 1	<u> Ui III</u>	1			ı
VOL	Low-level out	out voltage	$V_{DD}$ = min to max,	I <sub>OL</sub> = 1 mA			0.1	V
			$V_{DD} = 3.135 V,$	I <sub>OL</sub> = 16 mA			0.5	
			$V_{DD} = 3.135 \text{ V},$	AO = 1	-32	-52		ı
lOH	High-level out	put current	$V_{DD} = 3.3 \text{ V},$	V <sub>O</sub> 1.65 V		-51		mA
			$V_{DD} = 3.465 \text{ V},$	V <sub>C</sub> = 3.135 V		-14.5	-21	
			$V_{DD} = 3.135 \text{ V},$	V <sub>O</sub> = 1.95 V	43	61.5		Ī
lOL	Low-level out	out current	V <sub>DD</sub> = 3.3 V	<b>V</b> O = 1.65 V		65		mA
			$V_{DD} = 3.465 \text{ V}, \qquad V_{O} = 0.4 \text{ V}$			25.5	36	<u> </u>
loz	High-impedar current	ce-state output	S0 = 0, <b>6</b> 1 = <b>10</b>			±10	μΑ	
IOZ(STOP)	High-impedance-state output current during CLK stop		Stop 0 VO GN	D or V <sub>DD</sub>			±100	μΑ
IOZ(PD)	High-impedance-state output current in power-down state		PWRDNB € 0. V <sub>O</sub> ≡ GND or V <sub>DD</sub>		-10		100	μΑ
	High-level	REFCLK, PCLKM, SYNCLKN, STOPB	V <sub>DD</sub> = 3.465 V,	$V_I = V_{DD}$			10	^
Iн	input current	PWRDNB, S0, S1, S2, MULT0, MULT	V <sub>DD</sub> = 3.465 V,	$V_I = V_{DD}$			10	μΑ
	Low-level	REFCLK, PCLKM, SYNCLKN, STOPB	<b>V</b> 60 = 3.465 V,	V <sub>I</sub> = 0			-10	A
IIL	input current	PWRDNB, S0, S1, S2, MULT0, MULT1	V <sub>DD</sub> = 3.465 V,	V <sub>I</sub> = 0			-10	μΑ
7 -	Output	High state	R <sub>I</sub> at I <sub>O</sub> –14.5 mA to	o –16.5 mA	15	35	50	
Z <sub>O</sub>	impedance	Low state	R <sub>I</sub> at I <sub>O</sub> 14.5 mA to	16.5 mA	11	17	35	Ω
	Reference	V==10 V==100	\/ 2 465 \/	PWRDNB = 0			50	μΑ
	current	V <sub>DD</sub> IR V <sub>DD</sub> IPD	V <sub>DD</sub> = 3.465 V	PWRDNB = 1			0.5	mA
Cl	Input capacita	ince	$V_I = V_{DD}$ or GND			2		pF
CO	Output capac	tance	$V_O = V_{DD}$ or GND			3		pF
I <sub>DD(PD)</sub>	Supply curren	t in power-down state	REFCLK = 0 MHz to PWDNB = 0,	o 100 MHz, STOPB = 1			100	μΑ
IDD(CLKSTOP)	Supply curren	t in CLK stop state	BUSCLK configured	l for 400 MHz			30	mA
IDD(NORMAL)	Supply curren	t in normal state	BUSCLK = 400 MH:	Z			70	mA
(**************************************								

<sup>†</sup>  $V_{DD}$  refers to any of the following;  $V_{DD}$ ,  $V_{DD}IPD$ ,  $V_{DD}IR$ ,  $V_{DD}O$ ,  $V_{DD}C$ , and  $V_{DD}P$  ‡ All typical values are at  $V_{DD} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}C$ .



## switching characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	R		TEST CONDITIONS	MIN	TYPT MAX	UNIT
tc(out)	Clock output cycle time				2.5	3.75	ns
			267 MHz			80	
l.	Total cycle jitter over 1, 2,	Infinite and stopped phase alignment	300 MHz	05		70	
<sup>t</sup> (jitter)	3, 4, 5, or 6 clock cycles		356 MHz	See Figure 3		60	ps
			400 MHz	<b>S</b>		50	1
<sup>t</sup> (phase)	Phase detector phase erro	r for distributed lo	ор	Static phase error <sup>‡</sup>	-100	100	ps
t(phase, SSC)	PLL output phase error when tracking SSC			Dynamic phase ener <sup>‡</sup>	-100	100	ps
t(DC)	Output duty cycle over 10,000 cycles			See Figure 4	45%	55%	
(50)		Infinite and stopped phase alignment	267 MHz	4111		80	
	Output cycle-to-cycle		300 MHz	0.8		70	
<sup>t</sup> (DC, err)	duty cycle error		356 MHz	See Figure 5		60	ps
		g	400 MHz	2 4		50	
t <sub>r</sub> , t <sub>f</sub>	Output rise and fall times (measured at 20%–80% of output voltage)			See Figure 7	160	400	ps
Δt	Difference between rise an (20%–80%)  t <sub>f</sub> - t <sub>r</sub>	d fall times on a s	single device	See Figure 7		100	ps

<sup>†</sup> All typical values are at V<sub>DD</sub> = 3.3 V, T<sub>A</sub> = 25°C. ‡ Assured by design

## state transition latency specifications

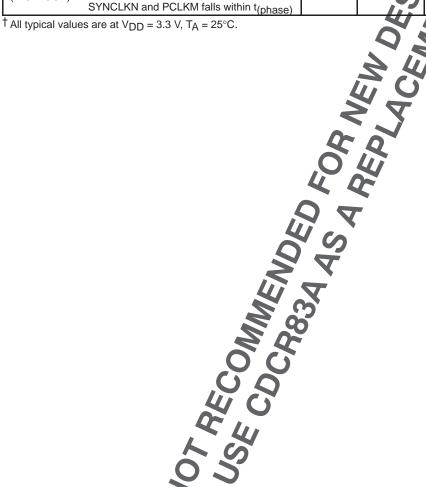
	PARAMETER	FROM	то	TEST CONDITIONS	MIN	TYP <sup>†</sup>	MAX	UNIT
	Delay time, PWRDNB↑ to CLK/CLKB output settled (excluding t(DISTLOCK))	Y	Name	See Figure 8			3	
<sup>t</sup> (powerup)	Delay time, PWRDNB↑ to internal PLV and clock are on and settled	Powerdown	Normal				3	ms
	Delay time, power up to CLK/CLKB output settled	.,	NI I	See Figure 8			3	
<sup>t</sup> (VDDpowerup)	Delay time, power up to internal RLL and clock are on and settled	V <sub>DD</sub>	Normal				3	ms
<sup>t</sup> (MULT)	MULT0 and MULT1 change to CLK CLKB output resettled (excluding (DIST COCK))	Normal	Normal	See Figure 9			1	ms
t(CLKON)	STOPB <sup>↑</sup> to CLK/CLKB/glitch-free clock edges	CLK Stop	Normal	See Figure 10			10	ns
<sup>t</sup> (CLKSETL)	STOPB to CLK/CLKB output settled to within 50 ps of the phase before STOPB was disabled	CLK Stop	Normal	See Figure 10			20	cycles
<sup>t</sup> (CLKOFF)	STOPB↓ to CLK/CLKB output disabled	Normal	CLK Stop	See Figure 10	_	_	5	ns

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{DD} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .



### state transition latency specifications (continued)

	PARAMETER	FROM	то	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
t(powerdown)	Delay time, PWRDNB↓ to the device in the power-down mode	Normal	Powerdown	See Figure 8			1	ms
t(STOP)	Maximum time in CLKSTOP (STOPB = 0) before reentering normal mode (STOPB = 1)	STOPB	Normal	See Figure 10			100	μs
t(ON)	Minimum time in normal mode (STOPB = 1) before reentering CLKSTOP (STOPB = 0)	Normal	CLK stop	See Figure 10	100			ms
<sup>t</sup> (DISTLOCK)	Time from when CLK/CLKB output is settled to when the phase error between SYNCLKN and PCLKM falls within t <sub>(phase)</sub>	Unlocked	Locked	NY			5	ms





### PARAMETER MEASUREMENT INFORMATION

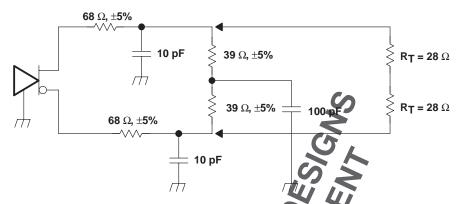
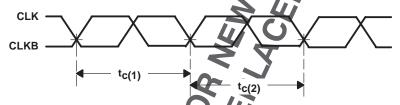
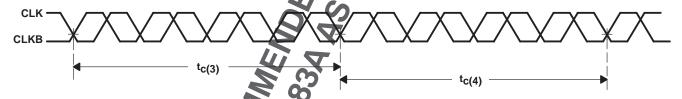


Figure 1. Test Load and Voltage Definitions ( $V_{O(X)}$ ,  $V_{O(X)}$ ,  $V_{O}$ ,  $V_{OH}$ ,  $V_{OL}$ )



Cycle-to-cycle jitter =  $|t_{C(1)} - t_{C(2)}|$  over 10000 consecutive cycles

Figure 2. Cycle to Cycle Jitter

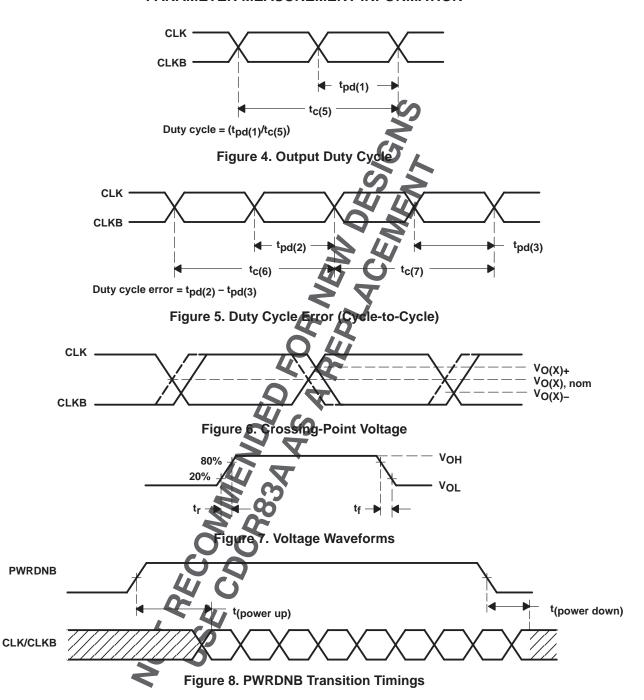


Cycle-to-cycle litter  $= t_{C(3)} - t_{C(4)}$  over 10000 consecutive cycles

Figure 3. Short Term Cycle-to-Cycle Jitter Over Four Cycles



#### PARAMETER MEASUREMENT INFORMATION





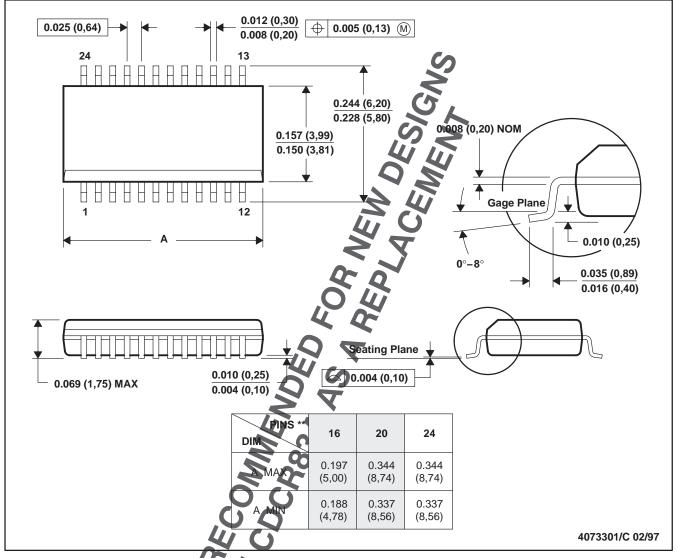
# PARAMETER MEASUREMENT INFORMATION MULT0 and/or MULT1 t(MULT) CLK/CLKB Figure 9. MULT Transition Timings t(ON) t(STOP) **STOPB** t(CLKSETL) t(CLKOFF) (see Note A) t(CLKON) (see Note A) **CLK/CLKB Output clock** Clock output settled not specified Clock enabled and glitch free within 50 ps of the glitches ok phase before disabled NOTE A: $V_{ref} = V_O \pm 200 \text{ mV}$ Figure 10. STOPE Transition Timings

#### **MECHANICAL DATA**

### DBQ (R-PDSO-G\*\*)

#### PLASTIC SMALL-OUTLINE PACKAGE

#### 24-PIN SHOWN



NOTES: A. All linear dimensions are in inches will meters).

B. This drawing is subject to change without notice.
C. Body dimensions do not include mole flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MO-13







.com 18-Jul-2006

#### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
CDCR83DBQ	NRND	SSOP/ QSOP	DBQ	24	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
CDCR83DBQG4	NRND	SSOP/ QSOP	DBQ	24	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
CDCR83DBQR	NRND	SSOP/ QSOP	DBQ	24	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
CDCR83DBQRG4	NRND	SSOP/ QSOP	DBQ	24	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

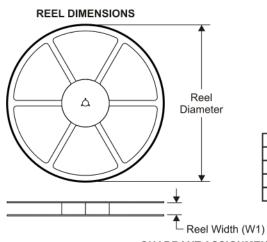
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

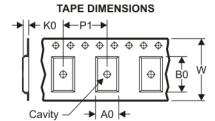
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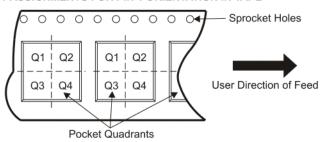
#### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCR83DBQR	SSOP/ QSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1





#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CDCR83DBQR	SSOP/QSOP	DBQ	24	2500	346.0	346.0	33.0

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